

Silicon Epitaxial Planar Diode

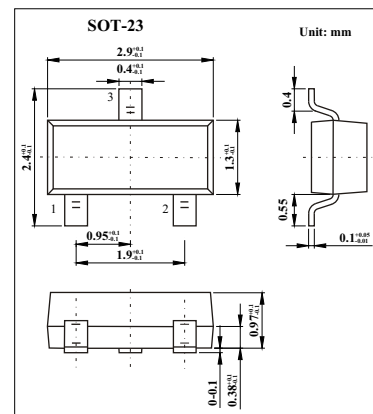
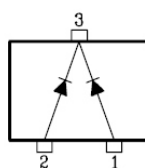
KDS184-RTK

Features

Low forward voltage : $V_{F(3)} = 0.9 \text{ V(Typ)}$

Fast reverse recovery time : $t_{rr} = 1.6\text{ns (MAX.)}$

Small total capacitance : $C_T = 0.9\text{pF(Typ)}$



Absolute Maximum Ratings $T_a = 25$

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Average forward current	I_O	100	mA
Maximum (peak) forward current	I_{FM}	300	mA
Surge current (10 ms)	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Junction Temperature	T_j	150	
Storage Temperature	T_{stg}	-55 to +150	

Electrical Characteristics $T_a = 25$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_{F(1)}$	$I_F = 1 \text{ mA}$		0.6		V
	$V_{F(2)}$	$I_F = 10 \text{ mA}$		0.72		
	$V_{F(3)}$	$I_F = 100 \text{ mA}$		0.90	1.20	
Reverse current	I_R	$V_R = 80 \text{ V}$			0.5	μA
Total capacitance	C_T	$V_R = 0, f = 1.0 \text{ MHz}$		0.9	3.0	pF
Reverse recovery time	t_{rr}	$I_F = 10 \text{ mA}$		1.6	4.0	ns

Marking

Marking	B3
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■ Typical Characteristics

